

# HiPerFET™ Power MOSFETs Q-CLASS

**IXFX 90N20Q**  
**IXFK 90N20Q**

$V_{DSS} = 200 \text{ V}$   
 $I_{D25} = 90 \text{ A}$   
 $R_{DS(on)} = 22 \text{ m}\Omega$

$t_{rr} \leq 200 \mu\text{s}$

Single MOSFET Die

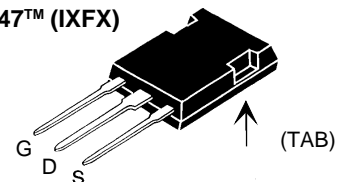
N-Channel Enhancement Mode

Avalanche Rated, Low  $Q_g$ , High  $dV/dt$ , Low  $t_{rr}$

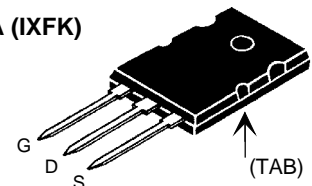


| Symbol    | Test Conditions   | Maximum Ratings |                  |
|-----------|---|-----------------|------------------|
| $V_{DSS}$ | $T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$   | 200             | V                |
| $V_{DGR}$ | $T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ ; $R_{GS} = 1 \text{ M}\Omega$  | 200             | V                |
| $V_{GS}$  | Continuous  | $\pm 20$        | V                |
| $V_{GSM}$ | Transient   | $\pm 30$        | V                |
| $I_{D25}$ | $T_C = 25^\circ\text{C}$  | 90              | A                |
| $I_{DM}$  | $T_C = 25^\circ\text{C}$ , pulse width limited by $T_{JM}$  | 360             | A                |
| $I_{AR}$  | $T_C = 25^\circ\text{C}$  | 90              | A                |
| $E_{AR}$  | $T_C = 25^\circ\text{C}$  | 60              | mJ               |
| $E_{AS}$  | $T_C = 25^\circ\text{C}$  | 2.5             | J                |
| $dv/dt$   | $I_S \leq I_{DM}$ , $di/dt \leq 100 \text{ A}/\mu\text{s}$ , $V_{DD} \leq V_{DSS}$<br>$T_J \leq 150^\circ\text{C}$ , $R_G = 2 \Omega$ | 5               | V/ns             |
| $P_D$     | $T_C = 25^\circ\text{C}$  | 500             | W                |
| $T_J$     |   | -55 ... +150    | $^\circ\text{C}$ |
| $T_{JM}$  |   | 150             | $^\circ\text{C}$ |
| $T_{stg}$ |   | -55 ... +150    | $^\circ\text{C}$ |
| $T_L$     | 1.6 mm (0.063 in.) from case for 10 s   | 300             | $^\circ\text{C}$ |
| $M_d$     | Mounting torque   | TO-264          | 0.4/6 Nm/lb.in.  |
| Weight    |   | PLUS 247        | 6 g              |
|           |   | TO-264          | 10 g             |

PLUS 247™ (IXFX)



TO-264 AA (IXFK)



G = Gate  
S = Source

D = Drain  
TAB = Drain

### Features

- IXYS advanced low  $Q_g$  process
- Low gate charge and capacitances  
- easier to drive  
- faster switching
- International standard packages
- Low  $R_{DS(on)}$
- Rated for unclamped Inductive load switching (UIS) rated
- Molding epoxies meet UL 94 V-0 flammability classification

### Applications

- DC-DC converters
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- AC motor control
- Temperature and lighting controls

### Advantages

- PLUS 247™ package for clip or spring mounting
- Space savings
- High power density

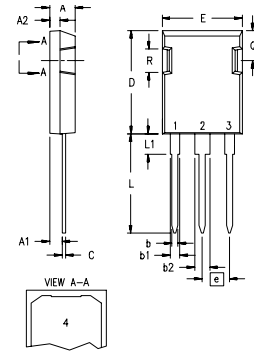
| Symbol       | Test Conditions   | Characteristic Values<br>( $T_J = 25^\circ\text{C}$ , unless otherwise specified) |      |                           |
|--------------|---|---|------|---------------------------|
|              |   | min.  | typ. | max.                      |
| $V_{DSS}$    | $V_{GS} = 0 \text{ V}$ , $I_D = 250 \mu\text{A}$                          | 200   |      | V                         |
| $V_{GS(th)}$ | $V_{DS} = V_{GS}$ , $I_D = 4 \text{ mA}$                                  | 2.0   |      | 4.0 V                     |
| $I_{GSS}$    | $V_{GS} = \pm 20 \text{ V}$ , $V_{DS} = 0$                                |   |      | $\pm 100 \text{ nA}$      |
| $I_{DSS}$    | $V_{DS} = V_{DSS}$<br>$V_{GS} = 0 \text{ V}$<br>$T_J = 125^\circ\text{C}$ |   |      | 100 $\mu\text{A}$<br>2 mA |
| $R_{DS(on)}$ | $V_{GS} = 10 \text{ V}$ , $I_D = 0.5 \cdot I_{D25}$<br>Note 1             |   |      | 22 m $\Omega$             |

| Symbol       | Test Conditions  | Characteristic Values  |      |      |
|--------------|--|--|------|------|
|              |  | $(T_J = 25^\circ\text{C}, \text{ unless otherwise specified})$ |      |      |
|              |  | min.   | typ. | max. |
| $g_{fs}$     | $V_{DS} = 10\text{ V}; I_D = 0.5 \cdot I_{D25}$ Note 1   | 40   | 50   | S    |
| $C_{iss}$    | $V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$  |  | 6800 | pF   |
| $C_{oss}$    |  |  | 1620 | pF   |
| $C_{rss}$    |  |  | 480  | pF   |
| $t_{d(on)}$  | $V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$<br>$R_G = 1\ \Omega$ (External), |  | 35   | ns   |
| $t_r$        |  |  | 31   | ns   |
| $t_{d(off)}$ |  |  | 82   | ns   |
| $t_f$        |  |  | 12   | ns   |
| $Q_{g(on)}$  | $V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$                                  |  | 190  | nC   |
| $Q_{gs}$     |  |  | 40   | nC   |
| $Q_{gd}$     |  |  | 90   | nC   |
| $R_{thJC}$   |  |  | 0.26 | K/W  |
| $R_{thCK}$   |  | 0.15   |      | K/W  |

| Source-Drain Diode |  | Characteristic Values  |      |               |
|--------------------|--|--|------|---------------|
|                    |  | $(T_J = 25^\circ\text{C}, \text{ unless otherwise specified})$ |      |               |
| Symbol             | Test Conditions  | min.   | typ. | max.          |
| $I_S$              | $V_{GS} = 0\text{ V}$  |  |      | 90 A          |
| $I_{SM}$           | Repetitive;<br>pulse width limited by $T_{JM}$                             |  |      | 360 A         |
| $V_{SD}$           | $I_F = I_S, V_{GS} = 0\text{ V}, \text{ Note 1}$                           |  |      | 1.3 V         |
| $t_{rr}$           | $I_F = 45\text{ A}, -di/dt = 100\text{ A}/\mu\text{s}, V_R = 100\text{ V}$ |  |      | 200 ns        |
| $Q_{RM}$           |  |  | 1.4  | $\mu\text{C}$ |
| $I_{RM}$           |  |  | 10   | A             |

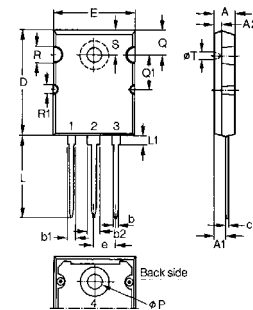
Note: 1. Pulse test,  $t \leq 300\ \mu\text{s}$ , duty cycle  $d \leq 2\%$

### PLUS247™ (IXFX) Outline



| Dim.           | Millimeter |       | Inches   |      |
|----------------|------------|-------|----------|------|
|                | Min.       | Max.  | Min.     | Max. |
| A              | 4.83       | 5.21  | .190     | .205 |
| A <sub>1</sub> | 2.29       | 2.54  | .090     | .100 |
| A <sub>2</sub> | 1.91       | 2.16  | .075     | .085 |
| b              | 1.14       | 1.40  | .045     | .055 |
| b <sub>1</sub> | 1.91       | 2.13  | .075     | .084 |
| b <sub>2</sub> | 2.92       | 3.12  | .115     | .123 |
| C              | 0.61       | 0.80  | .024     | .031 |
| D              | 20.80      | 21.34 | .819     | .840 |
| E              | 15.75      | 16.13 | .620     | .635 |
| e              | 5.45 BSC   |       | .215 BSC |      |
| L              | 19.81      | 20.32 | .780     | .800 |
| L1             | 3.81       | 4.32  | .150     | .170 |
| Q              | 5.59       | 6.20  | .220     | .244 |
| R              | 4.32       | 4.83  | .170     | .190 |

### TO-264 AA Outline



| Dim.           | Millimeter |       | Inches   |       |
|----------------|------------|-------|----------|-------|
|                | Min.       | Max.  | Min.     | Max.  |
| A              | 4.82       | 5.13  | .190     | .202  |
| A <sub>1</sub> | 2.54       | 2.89  | .100     | .114  |
| A <sub>2</sub> | 2.00       | 2.10  | .079     | .083  |
| b              | 1.12       | 1.42  | .044     | .056  |
| b <sub>1</sub> | 2.39       | 2.69  | .094     | .106  |
| b <sub>2</sub> | 2.90       | 3.09  | .114     | .122  |
| c              | 0.53       | 0.83  | .021     | .033  |
| D              | 25.91      | 26.16 | 1.020    | 1.030 |
| E              | 19.81      | 19.96 | .780     | .786  |
| e              | 5.46 BSC   |       | .215 BSC |       |
| J              | 0.00       | 0.25  | .000     | .010  |
| K              | 0.00       | 0.25  | .000     | .010  |
| L              | 20.32      | 20.83 | .800     | .820  |
| L1             | 2.29       | 2.59  | .090     | .102  |
| P              | 3.17       | 3.66  | .125     | .144  |
| Q              | 6.07       | 6.27  | .239     | .247  |
| Q <sub>1</sub> | 8.38       | 8.69  | .330     | .342  |
| R              | 3.81       | 4.32  | .150     | .170  |
| R <sub>1</sub> | 1.78       | 2.29  | .070     | .090  |
| S              | 6.04       | 6.30  | .238     | .248  |
| T              | 1.57       | 1.83  | .062     | .072  |

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,881,106 5,017,508 5,049,961 5,187,117 5,486,715 6,306,728B1  
4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025



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